

SILICON TUNING DIODES

... designed for electronic tuning of AM receivers and high capacitance, high tuning ratio applications.

- High Capacitance Ratio — $C_R = 15$ (Min),
MVAM108, 115, 125
- Guaranteed Diode Capacitance — $C_t = 440$ pF (Min) —
560 pF (Max) @ $V_R = 1.0$ Vdc, $f = 1.0$ MHz, MVAM108, MVAM115,
MVAM125
- Guaranteed Figure of Merit —
 $Q = 150$ (Min) @ $V_R = 1.0$ Vdc, $f = 1.0$ MHz

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Reverse Voltage	MVAM108 MVAM109 MVAM115 MVAM125	V_R	12 15 18 28	Volts
Forward Current		I_F	50	mA
Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C		P_D	280 2.8	mW mW/°C
Operating and Storage Junction Temperature Range		T_J, T_{stg}	-55 to +125	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, Each Device)

Characteristic	Symbol	Min	Typ	Max	Unit	
Breakdown Voltage ($I_R = 10 \mu\text{Adc}$)	MVAM108 MVAM109 MVAM115 MVAM125	$V_{(BR)R}$	12 15 18 28	— — — —	Vdc	
Reverse Current ($V_R = 8.0$ V) ($V_R = 9.0$ V) ($V_R = 15$ V) ($V_R = 25$ V)	MVAM108 MVAM109 MVAM115 MVAM125	I_R	— — — —	100 100 100 100	nAdc	
Diode Capacitance Temperature Coefficient (1) ($V_R = 1.0$ Vdc, $f = 1.0$ MHz, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$)		TC_C	—	435	ppm/°C	
Case Capacitance ($f = 1.0$ MHz, Lead Length 1/16")		C_C	—	0.18	pF	
Diode Capacitance ($V_R = 1.0$ Vdc, $f = 1.0$ MHz)	MVAM108, 115, 125 MVAM109	C_t	440 400	500 460	560 520	pF
Figure of Merit ($f = 1.0$ MHz, Lead Length 1/16", $V_R = 1.0$ Vdc)		Q	150	—	—	
Capacitance Ratio ($f = 1.0$ MHz)	MVAM108 MVAM109 MVAM115 MVAM125	C_1/C_8 C_1/C_9 C_1/C_{15} C_1/C_{25}	15 12 15 15	— — — —	— — — —	

NOTES:

1. The effect of increasing temperature 1.0°C , at any operating point, is equivalent to lowering the effective tuning voltage 1.25 mV. The percent change of capacitance per $^\circ\text{C}$ is nearly constant from -40°C to $+100^\circ\text{C}$.

<http://www.angelfire.com/electronic2/index1/>

MVAM108★
MVAM109★
MVAM115★
MVAM125★

CASE 182-02, STYLE 1
(TO-226AC)



2 0 — | | — 0 1
Cathode Anode

TUNING DIODES
WITH VERY HIGH
CAPACITANCE RATIO

★These are Motorola
designated preferred devices.

FIGURE 2 — CAPACITANCE versus REVERSE VOLTAGE

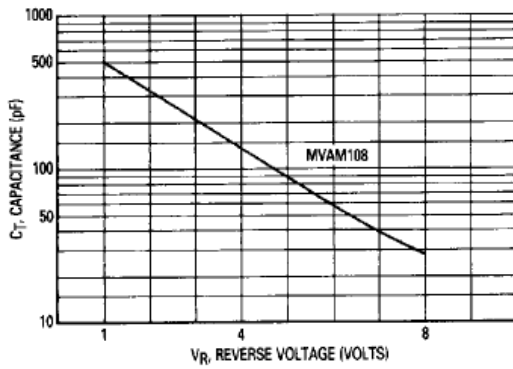


FIGURE 3 — CAPACITANCE versus REVERSE VOLTAGE

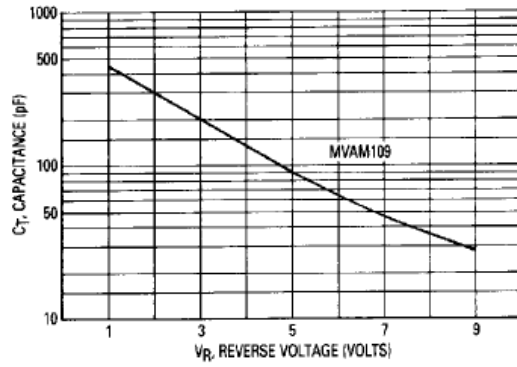


FIGURE 4 — CAPACITANCE versus REVERSE VOLTAGE

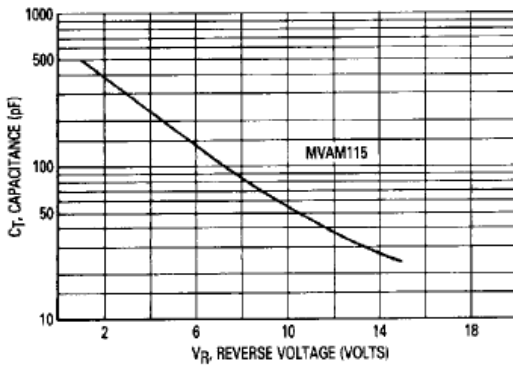
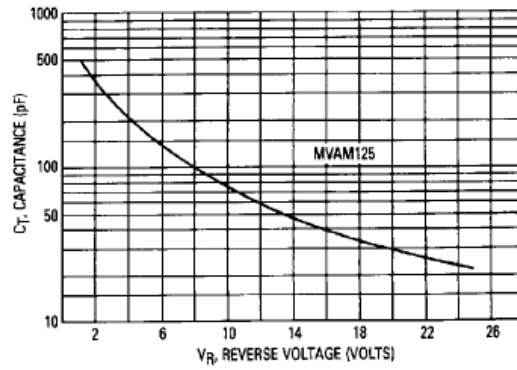


FIGURE 5 — CAPACITANCE versus REVERSE VOLTAGE



<http://www.angelfire.com/electronic2/index1/>